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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD SEMICONDUCTOR®

November 2013

FCI7N60

N-Channel SuperFET® MOSFET

600 V, 7 A, 600 mΩ

Features

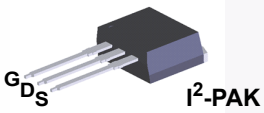
- 650V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 530 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 23 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 60 pF)
- 100% Avalanche Tested
- RoHS compliant

Application

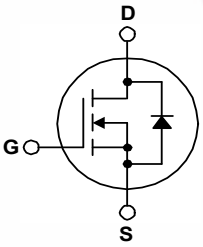
- Lighting
- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



I^2-PAK



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FCI7N60	Unit
V_{DSS}	Drain to Source Voltage		600	V
I_D	Drain Current	- Continuous (T_C = 25°C)	7	A
		- Continuous (T_C = 100°C)	4.4	
I_{DM}	Drain Current	- Pulsed (Note 1)	21	A
V_{GSS}	Gate to Source Voltage		±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		230	mJ
I_{AR}	Avalanche Current (Note 1)		7	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		8.3	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C)	83	W
		- Derate Above 25°C	0.67	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FCI7N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCI7N60	FCI7N60	I^2-PAK	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^oC$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA, T_C = 25°C	600	-	-	V
		V_{GS} = 0 V, I_D = 250 μA, T_C = 150°C	-	650	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	V_{GS} = 0 V, I_D = 7 A	-	700	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 600 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 480 V, T_C = 125°C	-	-	10	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 3.5 A	-	0.53	0.6	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 3.5 A	-	6	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	-	710	920	pF
C_{oss}	Output Capacitance		-	380	500	pF
C_{rss}	Reverse Transfer Capacitance		-	34	-	pF
C_{oss}	Output Capacitance	V_{DS} = 480 V, V_{GS} = 0 V, f = 1 MHz	-	22	29	pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	-	60	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 300 V, I_D = 7 A, V_{GS} = 10 V, R_G = 25 Ω (Note 4)	-	35	80	ns
t_r	Turn-On Rise Time		-	55	120	ns
$t_{d(off)}$	Turn-Off Delay Time		-	75	160	ns
t_f	Turn-Off Fall Time		-	32	75	ns
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 480 V, I_D = 7 A, V_{GS} = 10 V (Note 4)	-	23	30	nC
Q_{gs}	Gate to Source Gate Charge		-	4.2	5.5	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	11.5	-	nC
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	7	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	21	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 7 A	-	-	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 7 A, dI_F/dt = 100 A/μs	-	360	-	ns
Q_{rr}	Reverse Recovery Charge		-	4.5	-	μC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 3.5 A, V_{DD} = 50 V, R_G = 25Ω, starting T_J = 25°C.
3. I_{SD} ≤ 7 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

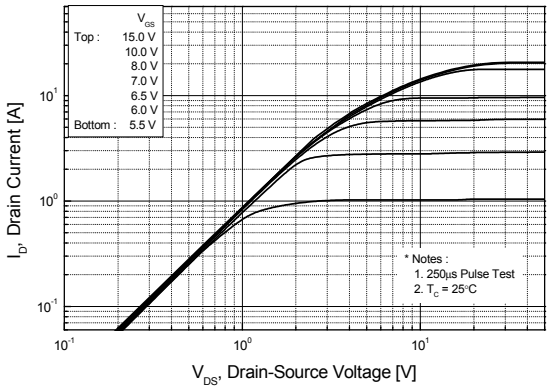


Figure 2. Transfer Characteristics

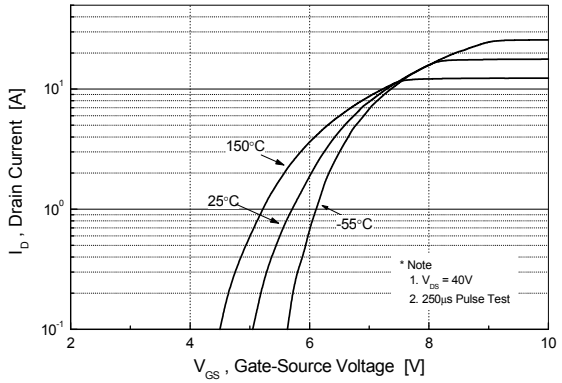


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

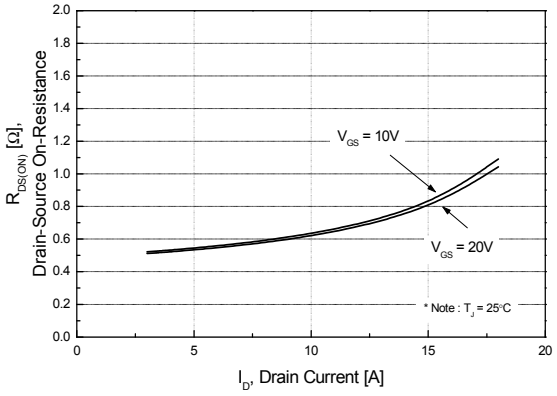


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

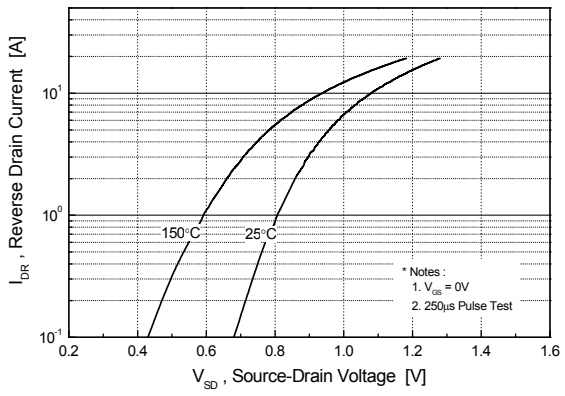


Figure 5. Capacitance Characteristics

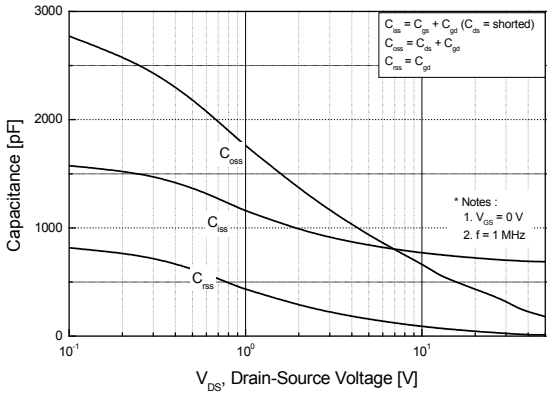
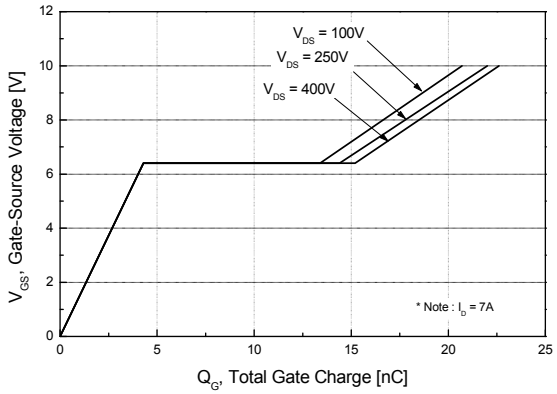


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

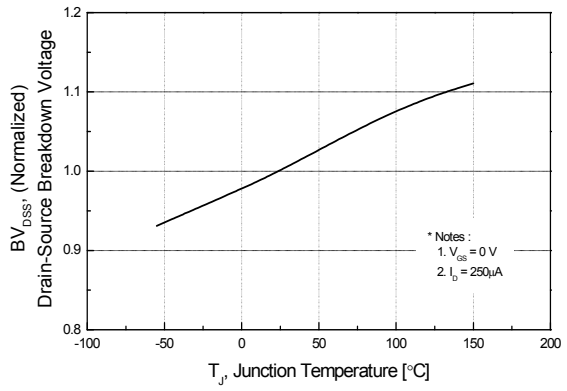


Figure 8. On-Resistance Variation vs. Temperature

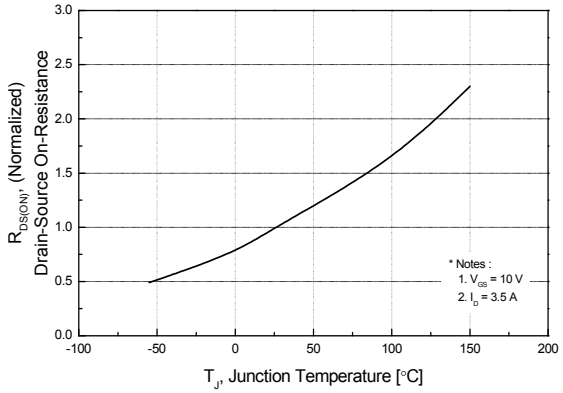


Figure 9. Maximum Safe Operating Area

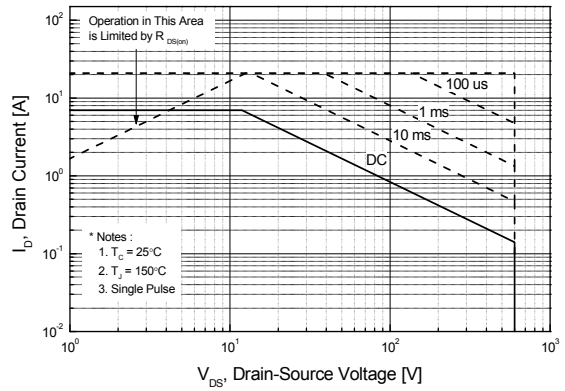


Figure 10. Maximum Drain Current vs. Case Temperature

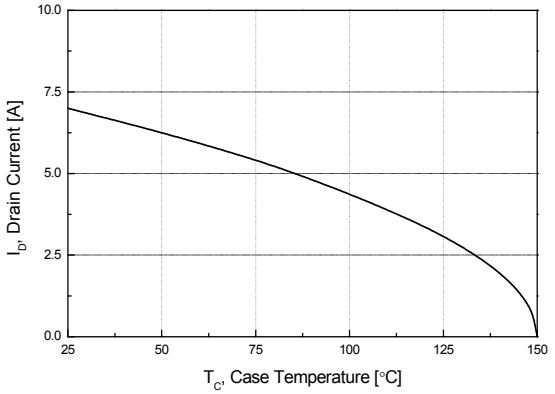
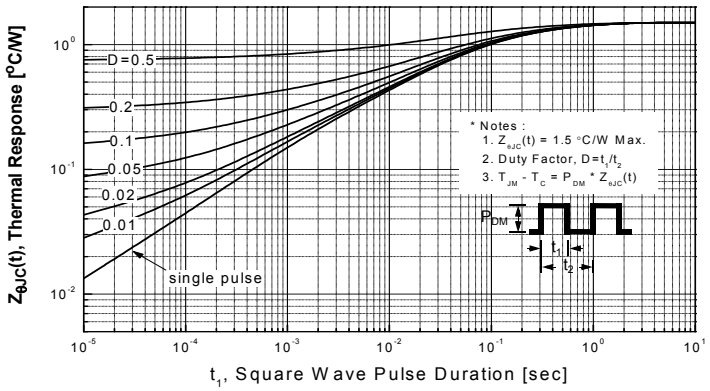


Figure 11. Transient Thermal Response Curve



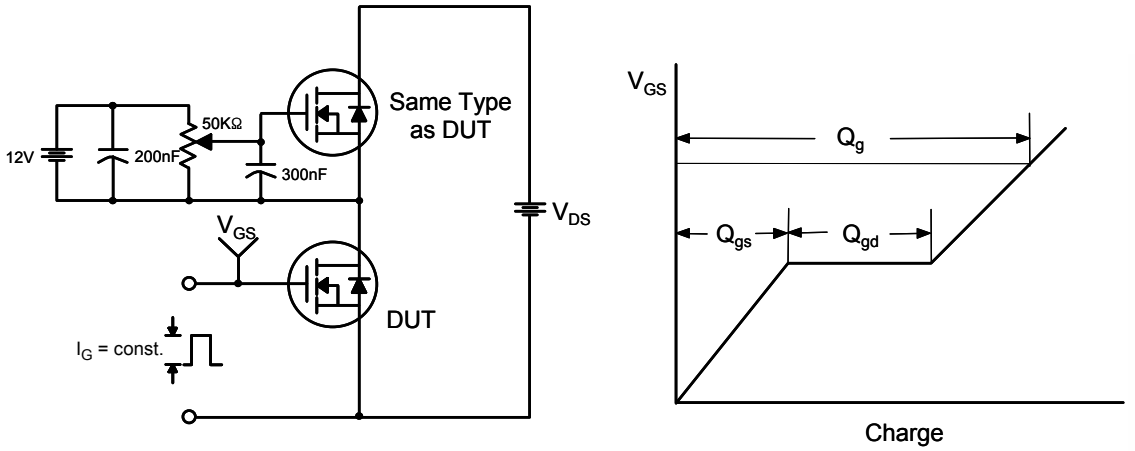


Figure 12. Gate Charge Test Circuit & Waveform

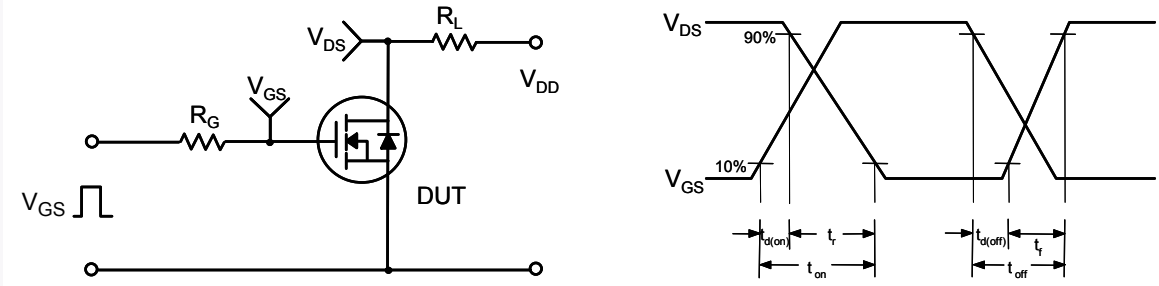


Figure 13. Resistive Switching Test Circuit & Waveforms

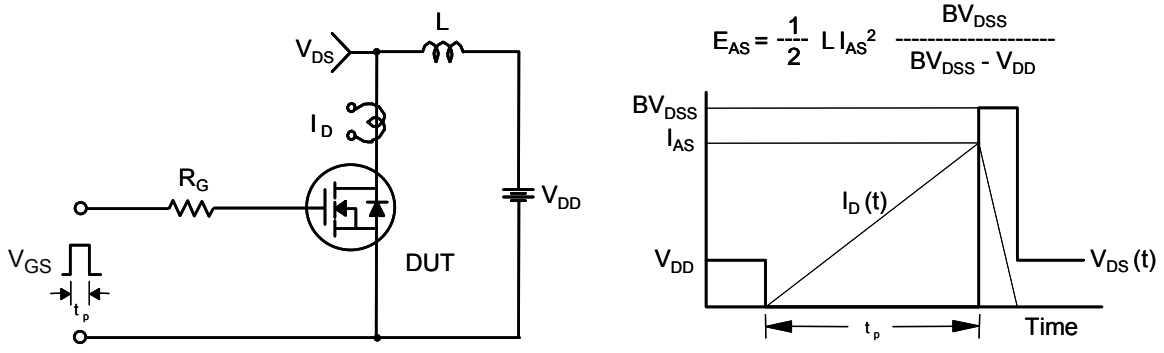


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

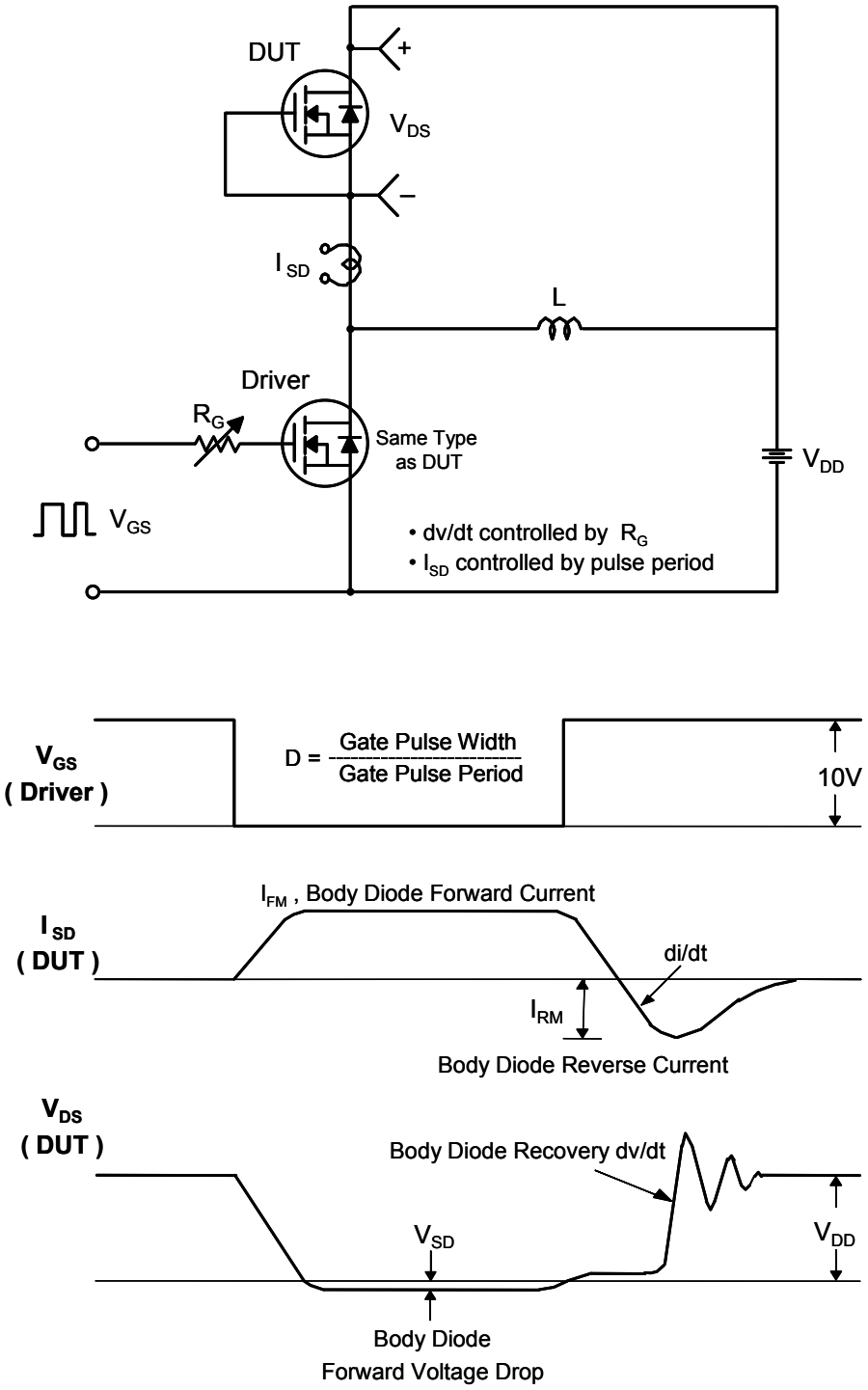
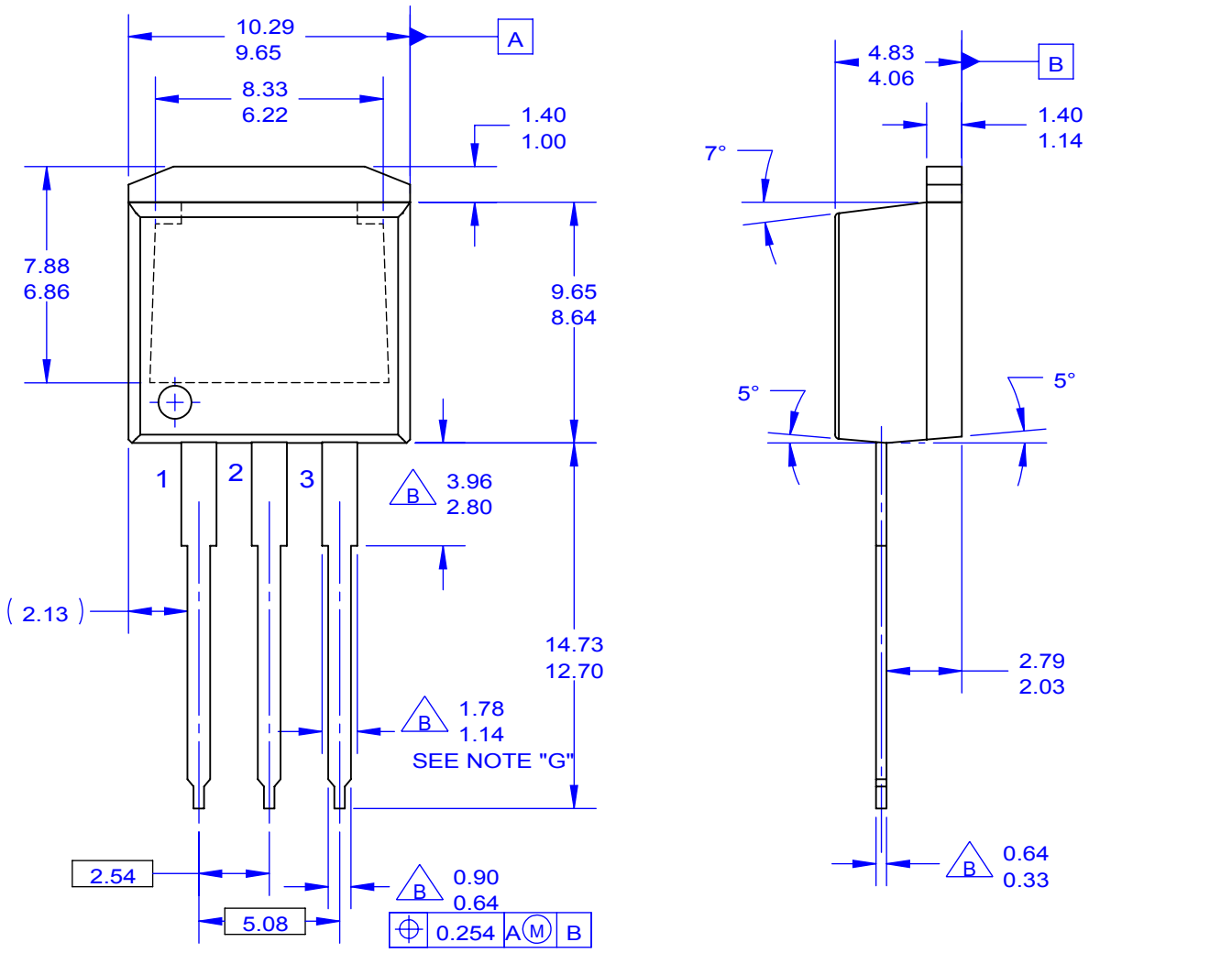


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO TO262 JEDEC VARIATION AA.
B DOES NOT COMPLY JEDEC STD. VALUE.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. DIMENSION AND TOLERANCE AS PER ANSI Y14.5-1994.
F. LOCATION OF PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF PACKAGE)
G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX.
H. DRAWING FILE NAME: TO262A03REV6

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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